

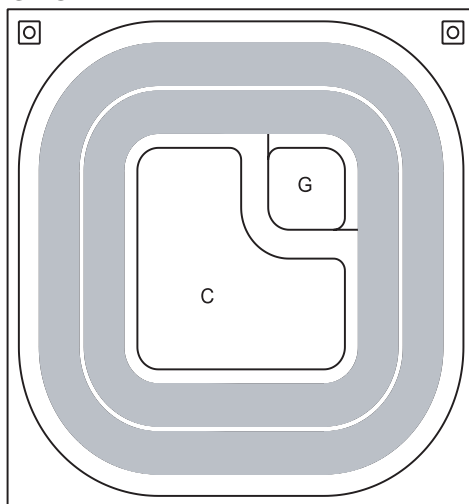
**PROCESS CPS057**  
**Silicon Controlled Rectifier**  
Sensitive Gate SCR Chip

**Central**<sup>TM</sup>  
Semiconductor Corp.

**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	57 x 57 MILS
Die Thickness	8.7 MILS ± 0.6 MILS
Cathode Bonding Pad Area	24 x 14 MILS
Gate Bonding Pad Area	7.9 x 7.9 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

**GEOMETRY**



BACKSIDE ANODE R0

**GROSS DIE PER 4 INCH WAFER**

3,374

**PRINCIPAL DEVICE TYPES**

CS39-4D

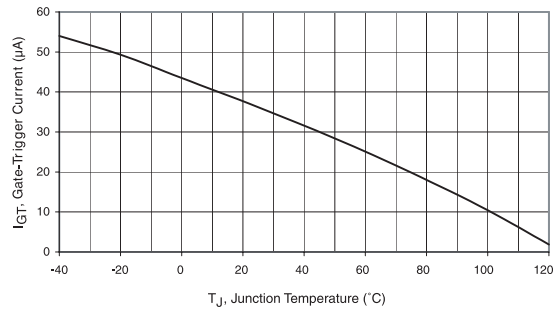
2N2323 thru 2N2329

CS223-4M

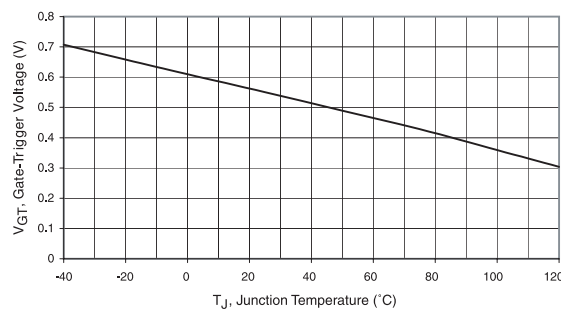
145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R1 (19 -May 2005)

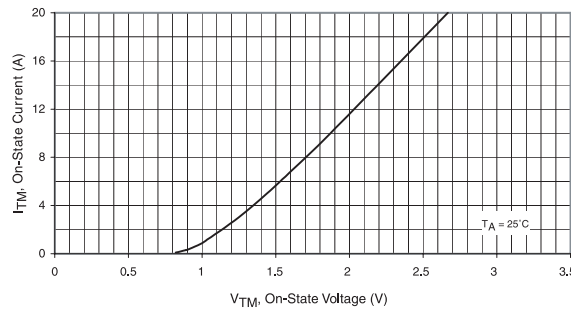
Typical Gate-Trigger Current



Typical Gate-Trigger Voltage



Typical On-State Voltage



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